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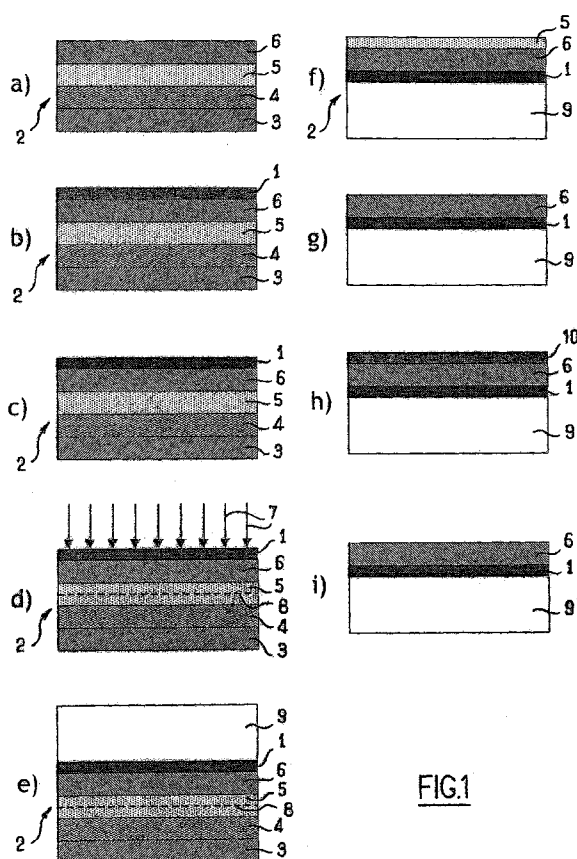
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(54) Title: PROCESS FOR FABRICATING A SUBSTRATE COMPRISING A DEPOSITED BURIED OXIDE LAYER



**FIG.1**

(57) Abstract: Process for fabricating a substrate comprising a buried oxide layer (1) for the production of electronic components or the like, which includes at least one step of depositing an oxide layer (1) or nitride layer on what is called a donor substrate (2) and/or a receiver substrate, and a step of bringing the donor substrate into contact with the receiver substrate (9); said process including at least a first heat treatment of the oxide layer (1) or nitride layer deposited on the donor substrate (2) and/or the receiver substrate, before bonding the donor substrate (2) to the receiver substrate (9), and a second heat treatment of the substrate consisting of the receiver substrate (9), the oxide layer (1) and all or part of the donor substrate (2), at a temperature equal to or higher than the temperature applied in the first heat treatment,. Substrate comprising at least an oxide or nitride layer (1) deposited on a donor substrate (2) and/or receiver substrate (9); the oxide or nitride layer (1) being degassed and having a refractive index smaller than the refractive index of an oxide or nitride layer of the same composition formed by thermal growth.

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